

ZXMN2A14FTA-VB Datasheet

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^e	Q _g (Typ.)			
	0.028 at V _{GS} = 4.5 V	6 ^a				
20	20 0.042 at V_{GS} = 2.5 V		8.8 nC			
	0.050 at V _{GS} = 1.8 V	5.6				

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications

ABSOLUTE MAXIMUM RATIN	IGS T _A = 25 °C,	unless otherwis	e noted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	± 12	V	
	T _C = 25 °C		6 ^a		
Continuous Droin Current (T 150 °C)	T _C = 70 °C		5.1		
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _A = 25 °C		5 ^{b, c}		
	T _A = 70 °C		4 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	20		
Continuous Source-Drain Diode Current	T _C = 25 °C		1.75		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	1.04 ^{b, c}		
	T _C = 25 °C		2.1		
Maximum Dawar Dissinction	T _C = 70 °C		1.3	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b, c}	vv	
	T _A = 70 °C	1	0.8 ^{b, c}		
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera	Ĭ	260			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	80	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	60			

Notes:

a. Package limited

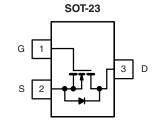
b. Surface Mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 125 °C/W.

e. Based on T_C = 25 °C.

FREE



Top View

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				71	1		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	1 050 - 4		25		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.45		1.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
		$V_{DS} = 20 V, V_{GS} = 0 V$			1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5$ V, $V_{GS} = 4.5$ V	20			Α	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5.0 \text{ A}$		0.028			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 4.7 \text{ A}$		0.042		Ω	
		$V_{GS} = 1.8 \text{ V}, \text{ I}_{D} = 4.3 \text{ A}$		0.050			
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 5.0 \text{ A}$		24		S	
Dynamic ^b	- I					<u> </u>	
Input Capacitance	C _{iss}			865		pF	
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		105			
Reverse Transfer Capacitance	C _{rss}			55			
		$V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 5.0 \text{ A}$		12	18	1	
Total Gate Charge	Qg			8.8	14	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 5.0 A		1.1			
Gate-Drain Charge	Q _{gd}			0.7			
Gate Resistance	Rg	f = 1 MHz	0.5	2.4	4.8	Ω	
Turn-On Delay Time	t _{d(on)}			8	16	-	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		17	26		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D} \cong$ 4 A, V_GEN = 4.5 V, R_g = 1 Ω		31	47		
Fall Time	t _f			8	16	ns	
Turn-On Delay Time	t _{d(on)}			5	10	110	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		13	20	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 4 \text{ A}, V_{GEN} = 5 \text{ V}, \text{ R}_g = 1 \Omega$		21	32		
Fall Time	t _f			6	12		
Drain-Source Body Diode Characteristic	s		<u></u>	•			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.75	۸	
Pulse Diode Forward Current	I _{SM}		T		20	A	
Body Diode Voltage	V _{SD}	$I_{S} = 4 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			12	20	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 4 A, dl/dt = 100 A/μs, T _J = 25 °C		5	10	nC	
Reverse Recovery Fall Time	t _a	$F = 4 \text{ A}, \text{ u/ul} = 100 \text{ A/}\mu\text{s}, T_{\text{J}} = 25 \text{ °C}$		7			
Reverse Recovery Rise Time	t _b			5		ns	

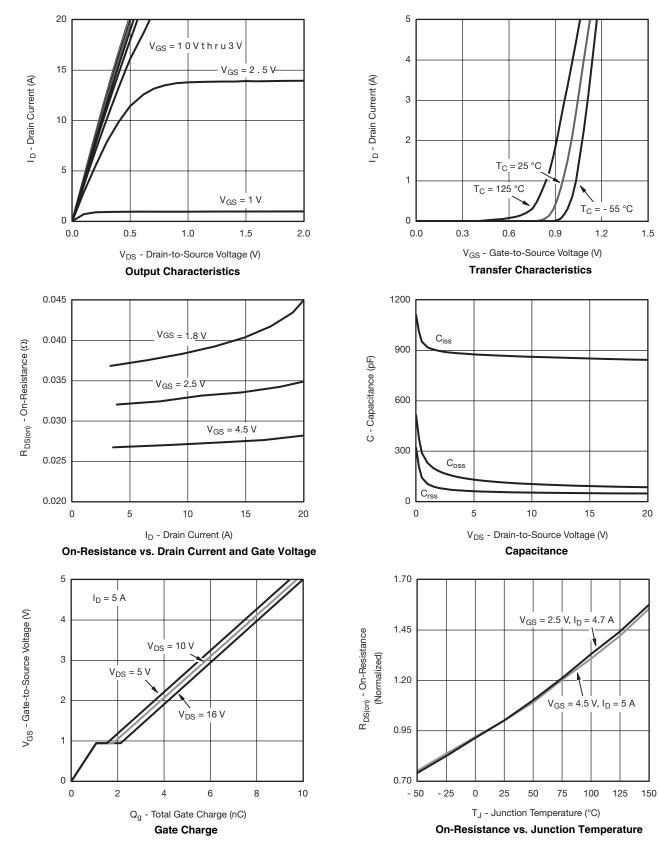
Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

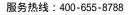




100 0.06 $I_D = 5 A$ $R_{DS(on)}$ - On-Resistance (Ω) 0.05 Is - Source Current (A) T_J = 150 °C 10 0.04 T_J = 125 °C $T_J = 25 \degree C$ 1 0.03 $T_J = 25 \ ^{\circ}C$ 0.1 0.02 0.0 0.3 0.6 0.9 1.2 0 2 4 6 8 V_{SD} - Source-to-Drain Voltage (V) V_{GS} - Gate-to-Source Voltage (V) Source-Drain Diode Forward Voltage On-Resistance vs. Gate-to-Source Voltage 0.9 32 0.7 24 $I_D = 250 \ \mu A$ V_{GS(th)} (V) Power (W) 0.5 16 0.3 8 0.1 0 - 25 - 50 0 25 50 75 100 125 150 0.001 0.01 0.1 1 10 100 Time (s) T_J - Temperature (°C) Single Pulse Power (Junction-to-Ambient) **Threshold Voltage** 100 Limited by R_{DS(on} 10 I_D - Drain Current (A) 100 µs ms 1 10 ms T_A = 25 °C 100 ms Single Pulse 0.1 10 **BVDSS** Limited 0.01 0.1 10 100 1 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

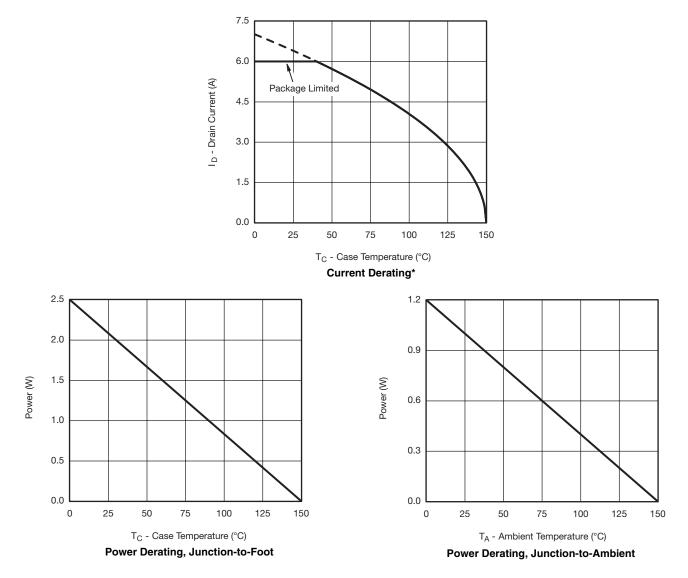
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





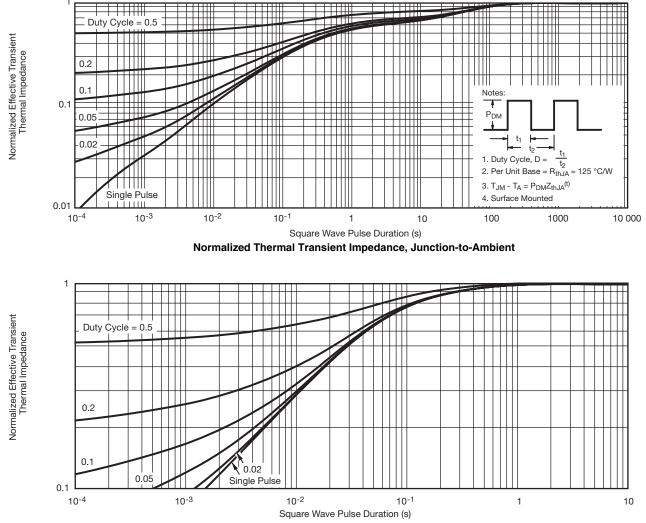
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

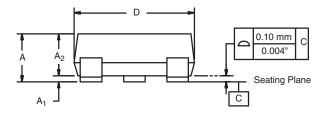


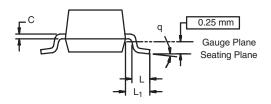
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD



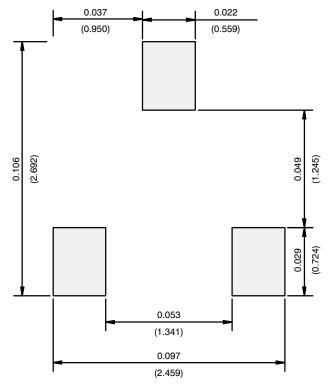




Dim	MILLIN	IETERS	INCHES		
	Min	Мах	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01				



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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